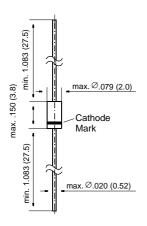
BAT85

Schottky Diodes

DO-35



Dimensions in inches and (millimeters)

FEATURES

- ♦ For general purpose applications.
- This diode features low turn-on voltage. The devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.
- This diode is also available in the MiniMELF case with type designation BAS85.

MECHANICAL DATA

Case: DO-35 Glass Case Weight: approx. 0.13 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit	
Continuous Reverse Voltage	V _R	30	V	
Forward Continuous Current at T _{amb} = 25 °C	IF	2001)	mA	
Peak Forward Current at T _{amb} = 25 °C	I _{FM}	3001)	mA	
Surge Forward Current at t _p < 1 s, T _{amb} = 25 °C	I _{FSM}	6001)	mA	
Power Dissipation at T _{amb} = 65 °C	P _{tot}	2001)	mW	
Junction Temperature	Tj	125	°C	
Ambient Operating Temperature Range	T _{amb}	-65 to +125	°C	
Storage Temperature Range	T _S	-65 to +150	°C	
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1) Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature.



BAT85

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Тур.	Max.	Unit
Reverse Breakdown Voltage tested with 10 μA Pulses	V _{(BR)R}	30	-	-	V
Forward Voltage Pulse Test $t_p < 300~\mu s, \delta < 2\%$ at $I_F = 0.1~m A$ at $I_F = 1~m A$ at $I_F = 10~m A$ at $I_F = 30~m A$ at $I_F = 100~m A$	VF VF VF VF	- - - -	- - - 0.5	0.24 0.32 0.4 - 0.8	V V V V
Leakage Current at V _R = 25 V	I _R	_	_	2	μΑ
Capacitance at $V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$	C _{tot}	_	-	10	pF
Thermal Resistance Junction to Ambient Air	R _{thJA}	_	_	0.431)	K/mW
Reverse Recovery Time from $I_F = 10$ mA to $I_R = 1$ mA	t _{rr}	_	_	5	ns

¹⁾ Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature.



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